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Origin of the bias stress instability in single-crystal OFETs VITALY PODZOROV, BUMSU LEE, DANIEL MASTROGIOVANNI, ALAN WAN, ERIC GARFUNKEL, Rutgers University — We report on the electrical transport and UPS measurements of organic single-crystal field-effect transistors that reveal the mechanism of the bias stress effect in these devices. Data on several compounds will be presented.

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